



NGTB10N60FG

N-Channel IGBT 600V, 10A, V_{CE(sat)};1.5V, TO-220F-3FS

ON Semiconductor®

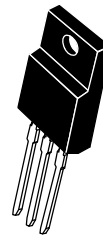
<http://onsemi.com>

Features

- IGBT V_{CE(sat)}=1.5V typ. (I_C=10A, V_{GE}=15V)
- IGBT I_C=20A (T_c=25°C)
- Adaption of full isolation type package
- 5μs short circuit capability
- Diode V_F=1.3V typ.(I_F=10A)
- Diode t_{rr}=70ns typ.
- Enhancement type

Applications

- Power factor correction of white goods appliance
- General purpose inverter



TO-220F-3FS

Specifications

Absolute Maximum Ratings at T_a = 25°C, Unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit	
Collector to Emitter Voltage	V _{CES}		600	V	
Gate to Emitter Voltage	V _{GES}		±20	V	
Collector Current (DC)	I _C ^{*1}	Limited by T _{jmax}	@ T _c =25°C ^{*2}	20	A
			@ T _c =100°C ^{*2}	10	A
Collector Current (Pulse)	I _{CP}	Pulse width Limited by T _{jmax}	72	A	
Diode Average Output Current	I _O		10	A	
Allowable Power Dissipation	P _D	T _c =25°C (Our ideal heat dissipation condition) ^{*2}	40	W	
Junction Temperature	T _j		150	°C	
Storage Temperature	T _{stg}		- 55 to +150	°C	

Note : *1 Collector Current is calculated from the following formula.

$$I_C(T_c) = \frac{T_{jmax} - T_c}{R_{th(j-c)}} \times V_{CE(sat)}(I_C(T_c))$$

*2 Our condition is radiation from backside.

The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Electrical Characteristics

 at T_a = 25°C, Unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Collector to Emitter Breakdown Voltage	V _{(BR)CES}	I _C =500μA, V _{GE} =0V	600			V
Collector to Emitter Cut off Current	I _{CES}	V _{CE} =600V, V _{GE} =0V	T _c =25°C		10	μA
			T _c =125°C		1	mA
Gate to Emitter Leakage Current	I _{GES}	V _{GE} =±20V, V _{CE} =0V			±100	nA
Gate to Emitter Threshold Voltage	V _{GE(off)}	V _{CE} =20V, I _C =250μA	4.5		6.5	V
Collector to Emitter Saturation Voltage	V _{CE(sat)}	V _{GE} =15V, I _C =10A	T _c =25°C	1.5	1.7	V
			T _c =125°C	1.7		V
Diode Forward Voltage	V _F	I _F =10A		1.3		V
Input Capacitance	C _{ies}	V _{CE} =20V, f=1MHz		1440		pF
Output Capacitance	C _{oes}			60		pF
Reverse Transfer Capacitance	C _{res}			30		pF

ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

Continued on next page.

NGTB10N60FG

Continued from preceding page.

Parameter	Symbol	Conditions	Value			Unit
			min	typ	max	
Turn-ON Delay Time	$t_{d(on)}$			40		ns
Rise Time	t_r	$V_{CC}=300V, I_C=10A$		23		ns
Turn-ON Time	t_{on}	$R_G=30\Omega, L=200\mu H$		110		ns
Turn-OFF Delay Time	$t_{d(off)}$	$V_{GE}=0V/15V$		145		ns
Fall Time	t_f	$V_{clamp}=400V$		90		ns
Turn-OFF Time	t_{off}	See Fig.1, See Fig.2		240		ns
Total Gate Charge	Q_g			55		nC
Gate to Emitter Charge	Q_{ge}	$V_{CE}=300V, V_{GE}=15V, I_C=10A$		20		nC
Gate to Collector "Miller" Charge	Q_{gc}			10		nC
Diode Reverse Recovery Time	t_{rr}	$I_F=10A, di/dt=100A/\mu s, V_{CC}=50V$, See Fig.3		70		ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Thermal Characteristics at $T_a = 25^\circ C$, Unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Thermal Resistance IGBT (junction- Case)	$R_{th(j-c)}$ (IGBT)	$T_c=25^\circ C$ (Our ideal heat dissipation condition)*2	3.09	$^\circ C / W$
Thermal Resistance Diode (junction- Case)	$R_{th(j-c)}$ (Diode)	$T_c=25^\circ C$ (Our ideal heat dissipation condition)*2	4	$^\circ C / W$
Thermal Resistance (junction- ambient)	$R_{th(j-a)}$		59.5	$^\circ C / W$

Fig.1 Switching Time Test Circuit

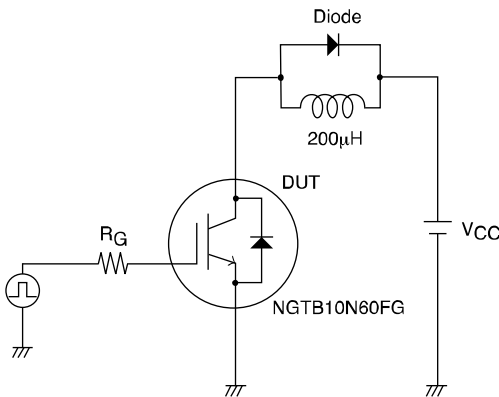
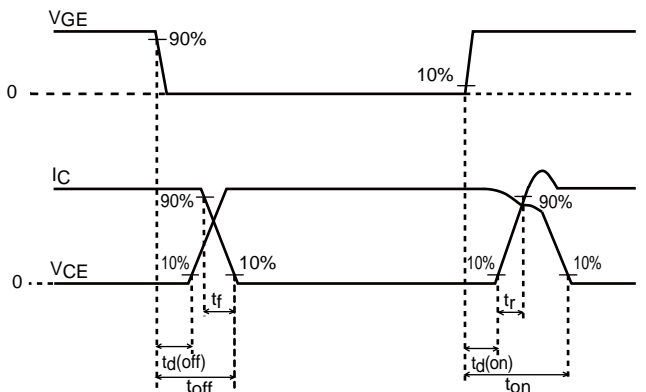
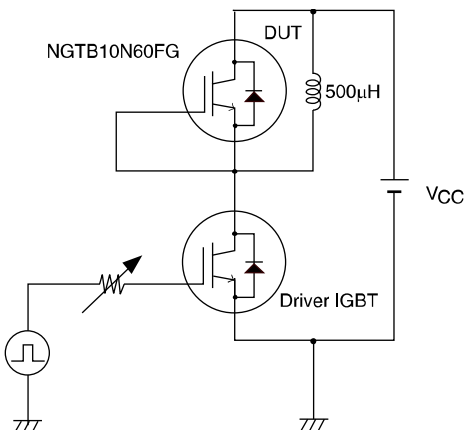


Fig.2 Timing Chart

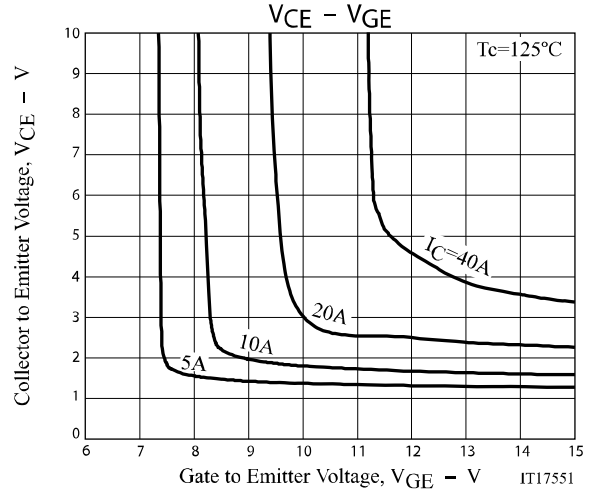
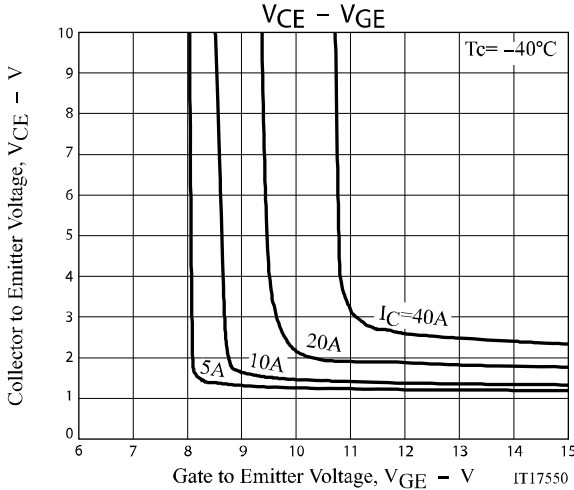
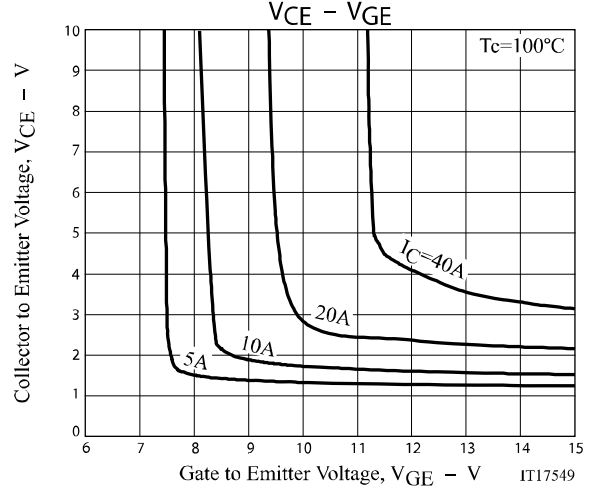
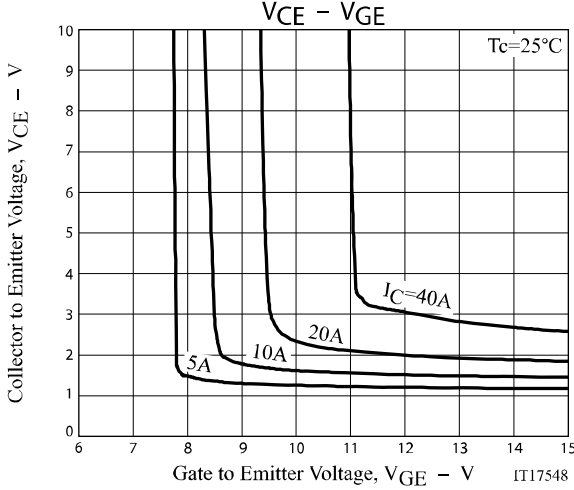
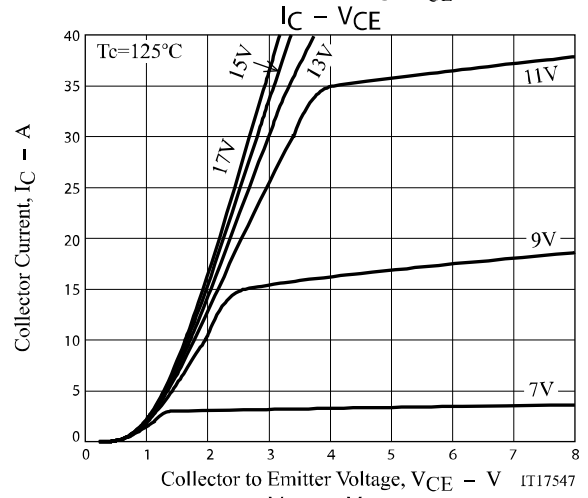
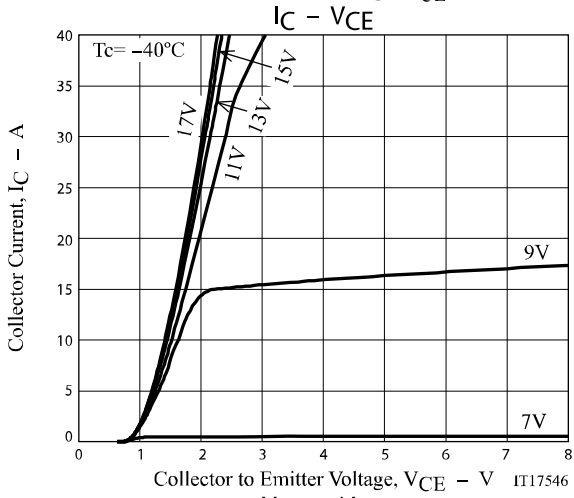
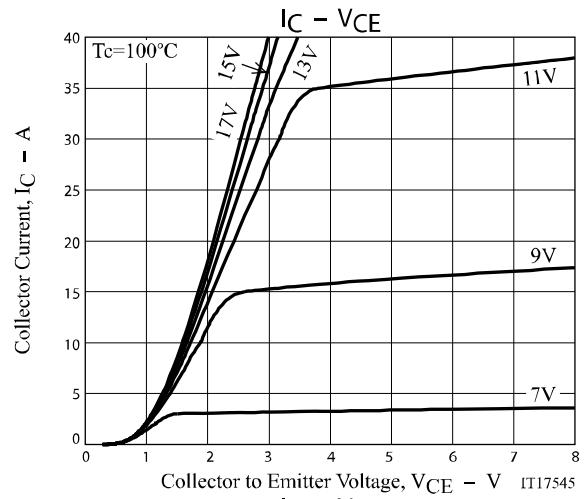
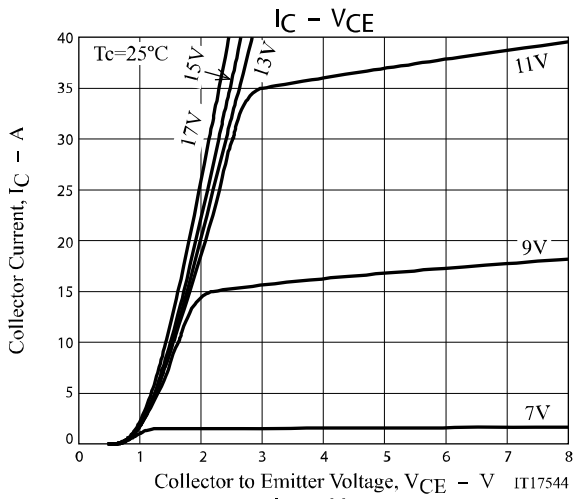


IT16383

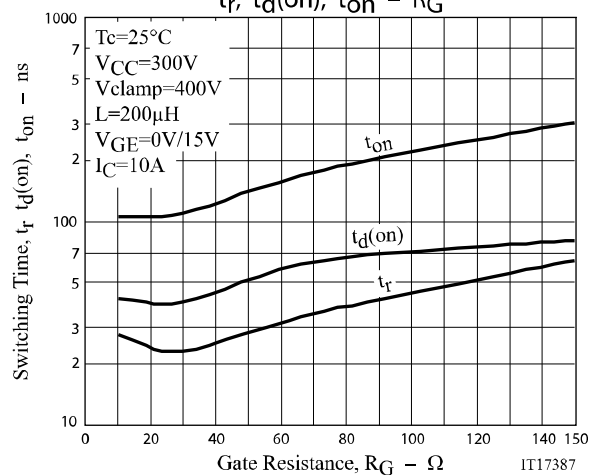
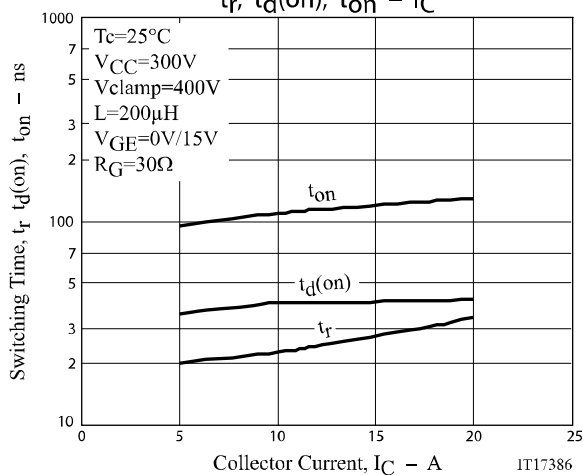
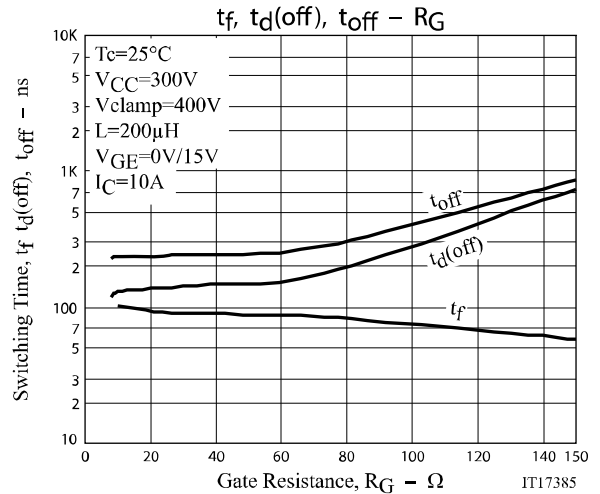
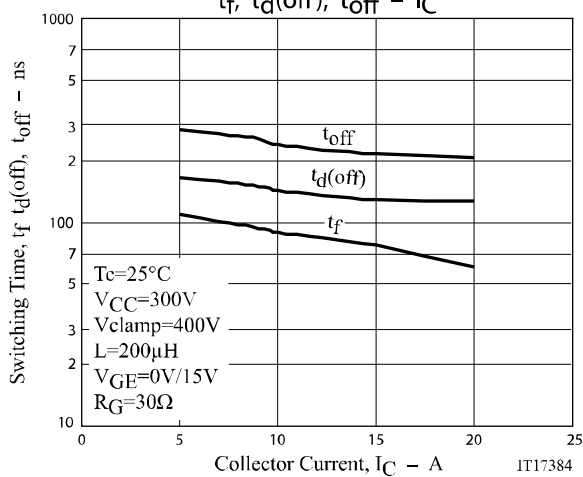
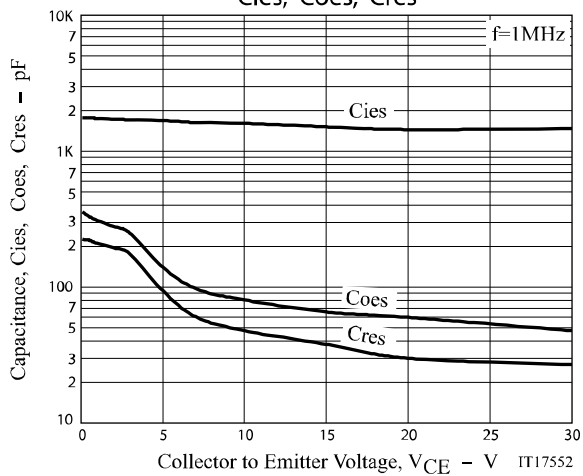
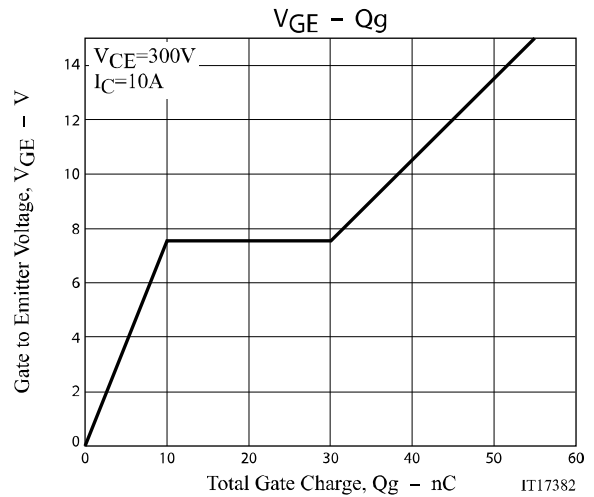
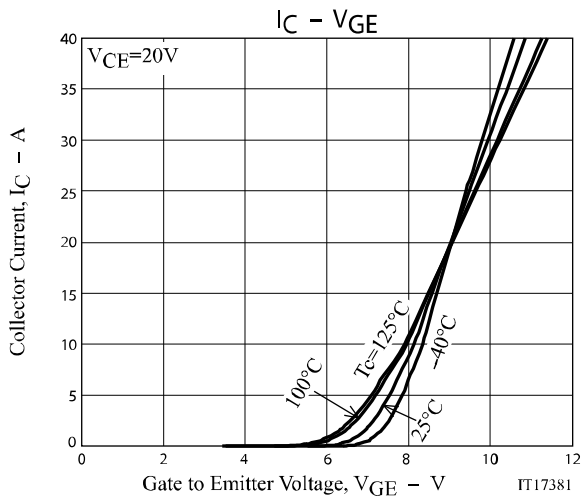
Fig.3 Reverse Recovery Time Test Circuit



NGTB10N60FG



NGTB10N60FG



NGTB10N60FG

